74AVC16T245

16-bit dual supply translating transceiver with configurable voltage translation; 3-state

Rev. 6 — 9 September 2013

Product data sheet

1. General description

The 74AVC16T245 is a 16-bit transceiver with bidirectional level voltage translation and 3-state outputs. The device can be used as two 8-bit transceivers or as a 16-bit transceiver. It has dual supplies ($V_{CC(A)}$ and $V_{CC(B)}$) for voltage translation and four 8-bit input-output ports (nAn and nBn) each with its own output enable (n \overline{OE}) and send/receive (nDIR) input for direction control. $V_{CC(A)}$ and $V_{CC(B)}$ can be independently supplied at any voltage between 0.8 V and 3.6 V making the device suitable for low voltage translation between any of the following voltages: 0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V. A HIGH on nDIR selects transmission from nAn to nBn while a LOW on nDIR selects transmission from nBn to nAn. A HIGH on $n\overline{OE}$ causes the outputs to assume a high-impedance OFF-state

The device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In suspend mode when either $V_{CC(A)}$ or $V_{CC(B)}$ are at GND level, both nAn and nBn are in the high-impedance OFF-state.

2. Features and benefits

- Wide supply voltage range:
 - V_{CC(A)}: 0.8 V to 3.6 V
 - ◆ V_{CC(B)}: 0.8 V to 3.6 V
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3B exceeds 8000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101D exceeds 1000 V
- Maximum data rates:
 - ◆ 380 Mbit/s (≥ 1.8 V to 3.3 V translation)
 - ◆ 200 Mbit/s (≥ 1.1 V to 3.3 V translation)
 - 200 Mbit/s (≥ 1.1 V to 2.5 V translation)
 - 200 Mbit/s (≥ 1.1 V to 1.8 V translation)
 - 150 Mbit/s (≥ 1.1 V to 1.5 V translation)



- ◆ 100 Mbit/s (≥ 1.1 V to 1.2 V translation)
- Suspend mode
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

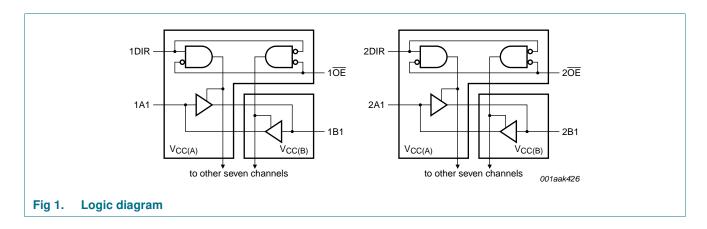
3. Ordering information

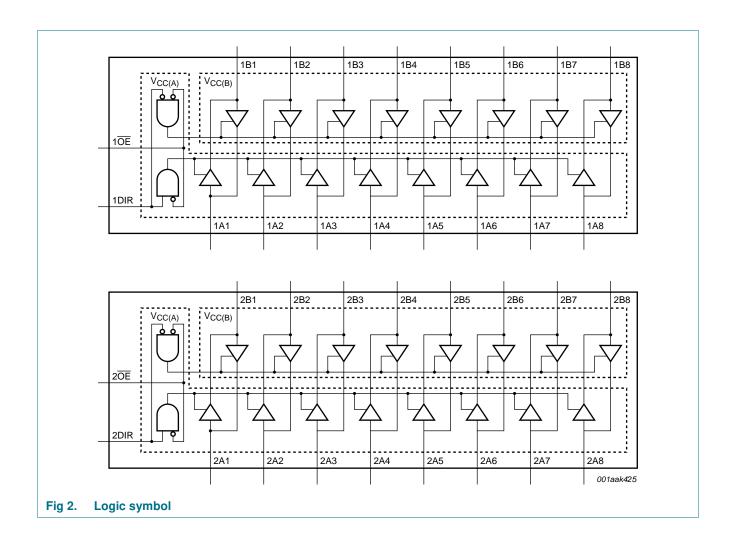
Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AVC16T245DGG	–40 °C to +125 °C	TSSOP48	plastic thin shrink small outline package; 48 leads; body width 6.1 mm	SOT362-1
74AVC16T245DGV	–40 °C to +125 °C	TSSOP48[1]	plastic thin shrink small outline package; 48 leads; body width 4.4 mm; lead pitch 0.4 mm	SOT480-1
74AVC16T245EV	–40 °C to +125 °C	VFBGA56	plastic very thin fine-pitch ball grid array package; 56 balls; body $4.5\times7\times0.65~mm$	SOT702-1
74AVC16T245BX	–40 °C to +125 °C	HXQFN60	plastic compatible thermal enhanced extremely thin quad flat package; no leads; 60 terminals; body $4\times6\times0.5$ mm	SOT1134-2

^[1] Also known as TVSOP48.

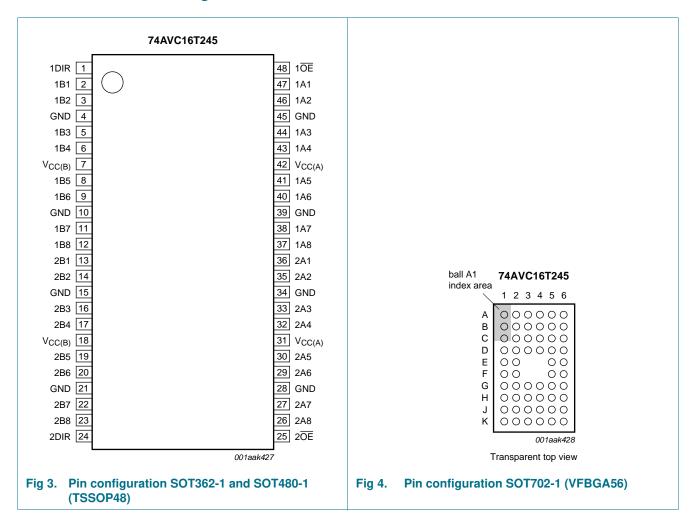
4. Functional diagram

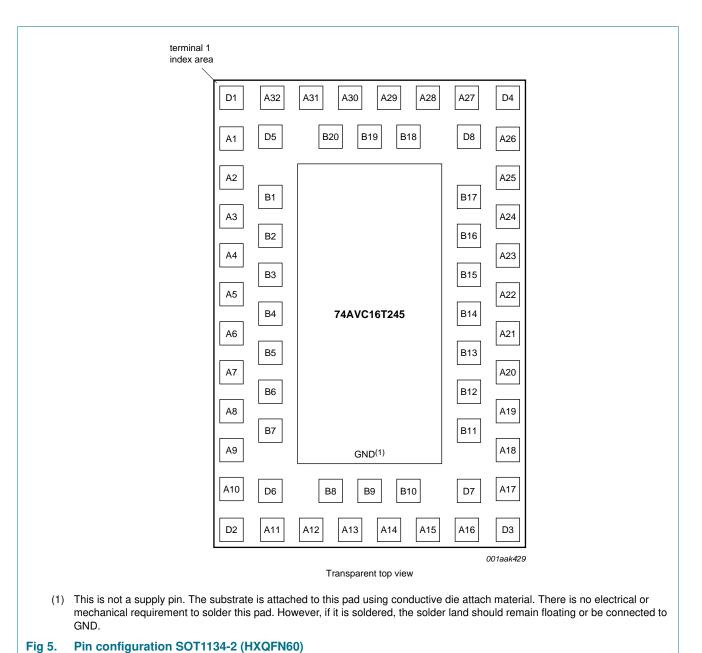




5. Pinning information

5.1 Pinning





5.2 Pin description

Table 2. Pin description

Symbol	Pin			Description
	SOT362-1 and SOT480-1	SOT702-1	SOT1134-2	
1DIR, 2DIR	1, 24	A1, K1	A30, A13	direction control
1B1 to 1B8	2, 3, 5, 6, 8, 9, 11, 12	B2, B1, C2, C1, D2, D1, E2, E1	B20, A31, D5, D1, A2, B2, B3, A5	data input or output
2B1 to 2B8	13, 14, 16, 17, 19, 20, 22, 23	F1, F2, G1, G2, H1, H2, J1, J2	A6, B5, B6, A9, D2, D6, A12, B8	data input or output
GND <u>¹¹</u>	4, 10, 15, 21, 28, 34, 39, 45	B3, D3, G3, J3, J4, G4, D4, B4	A32, A3, A8, A11, A16, A19, A24, A27	ground (0 V)
$V_{CC(B)}$	7, 18	C3, H3	A1, A10	supply voltage B (nBn inputs are referenced to $V_{\text{CC(B)}}$)
10E, 20E	48, 25	A6, K6	A29, A14	output enable input (active LOW)
1A1 to 1A8	47, 46, 44, 43, 41, 40, 38, 37	B5, B6, C5, C6, D5, D6, E5, E6	B18, A28, D8, D4, A25, B16, B15, A22	data input or output
2A1 to 2A8	36, 35, 33, 32, 30, 29, 27, 26	F6, F5, G6, G5, H6, H5, J6, J5	A21, B13, B12, A18, D3, D7, A15, B10	data input or output
$V_{CC(A)}$	31, 42	C4, H4	A17, A26	supply voltage A (nAn, n $\overline{\text{OE}}$ and nDIR inputs are referenced to $V_{\text{CC(A)}}$)
n.c.	-	A2, A3, A4, A5, K2, K3, K4, K5	A4, A7, A20, A23, B1, B4, B7, B9, B11, B14, B17, B19	not connected

^[1] All GND pins must be connected to ground (0 V).

6. Functional description

Table 3. Function table[1]

Supply voltage	Input	Input		Input/output[3]		
V _{CC(A)} , V _{CC(B)}	nOE[2]	nDIR[2]	nAn[2]	nBn[2]		
0.8 V to 3.6 V	L	L	nAn = nBn	input		
0.8 V to 3.6 V	L	Н	input	nBn = nAn		
0.8 V to 3.6 V	Н	Χ	Z	Z		
GND[3]	Χ	Χ	Z	Z		

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

^[2] The nAn, nDIR and n $\overline{\text{OE}}$ input circuit is referenced to $V_{\text{CC(A)}}$; The nBn input circuit is referenced to $V_{\text{CC(B)}}$.

^[3] If at least one of $V_{CC(A)}$ or $V_{CC(B)}$ is at GND level, the device goes into suspend mode.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

		• • • • • • • • • • • • • • • • • • • •	•		,
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{\text{CC}(A)}$	supply voltage A		-0.5	+4.6	V
$V_{CC(B)}$	supply voltage B		-0.5	+4.6	V
I _{IK}	input clamping current	$V_I < 0 V$	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode	[1][2][3] -0.5	$V_{CCO} + 0.5$	V
		Suspend or 3-state mode	<u>[1]</u> –0.5	+4.6	V
I _O	output current	$V_O = 0 V \text{ to } V_{CCO}$	[2] _	±50	mA
I _{CC}	supply current	per $V_{CC(A)}$ or $V_{CC(B)}$ pin	-	100	mA
I _{GND}	ground current	per GND pin	-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C};$			
		TSSOP48 package	<u>[4]</u> _	500	mW
		VFBGA56 package	<u>[5]</u> _	1000	mW
		HXQFN60 package	<u>[5]</u> _	1000	mW

^[1] The minimum input voltage ratings and output voltage ratings may be exceeded if the input and output current ratings are observed.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		0.8	3.6	V
$V_{CC(B)}$	supply voltage B		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	[1] 0	V_{CCO}	V
		Suspend or 3-state mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CCI} = 0.8 \text{ V to } 3.6 \text{ V}$	[2] _	5	ns/V

^[1] V_{CCO} is the supply voltage associated with the output port.

^[2] V_{CCO} is the supply voltage associated with the output port.

^[3] $V_{CCO} + 0.5 V$ should not exceed 4.6 V.

^[4] Above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.

^[5] Above 70 °C the value of P_{tot} derates linearly with 1.8 mW/K.

^[2] V_{CCI} is the supply voltage associated with the input port.

9. Static characteristics

Table 6. Typical static characteristics at $T_{amb} = 25 \, {}^{\circ}C_{1}^{1}$

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$	-	0.69	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = 1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$	-	0.07	-	V
lı	input leakage current	nDIR, n \overline{OE} input; V _I = 0 V or 3.6 V; V _{CC(A)} = V _{CC(B)} = 0.8 V to 3.6 V	-	±0.025	±0.25	μА
l _{OZ}	OFF-state output current	A or B port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 3.6$ V	[3] _	±0.5	±2.5	μА
		suspend mode A port; $V_O = 0 \ V \ or \ V_{CCO}$; $V_{CC(A)} = 3.6 \ V$; $V_{CC(B)} = 0 \ V$	[3]	±0.5	±2.5	μА
		suspend mode B port; $V_O = 0 \text{ V or } V_{CCO}$; $V_{CC(A)} = 0 \text{ V}$; $V_{CC(B)} = 3.6 \text{ V}$	[3] _	±0.5	±2.5	μА
I _{OFF}	power-off leakage current	A port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	±0.1	±1	μА
		B port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0.8$ V to 3.6 V	-	±0.1	±1	μА
C _I	input capacitance	nDIR, n \overline{OE} input; V _I = 0 V or 3.3 V; V _{CC(A)} = V _{CC(B)} = 3.3 V	-	2.0	-	pF
C _{I/O}	input/output capacitance	A and B port; $V_O = 3.3 \text{ V or } 0 \text{ V}$; $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$	-	4.5	-	pF

^[1] V_{CCO} is the supply voltage associated with the output port.

Table 7. Static characteristics [1][2]

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to	+85 °C	-40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
V_{IH}	HIGH-level	data input					
	input voltage	V _{CCI} = 0.8 V	0.70V _{CCI}	-	0.70V _{CCI}	-	V
		V _{CCI} = 1.1 V to 1.95 V	0.65V _{CCI}	-	0.65V _{CCI}	-	V
		V _{CCI} = 2.3 V to 2.7 V	1.6	-	1.6	-	V
		$V_{CCI} = 3.0 \text{ V to } 3.6 \text{ V}$	2	-	2	-	٧
		nDIR, nOE input					
		$V_{CC(A)} = 0.8 \text{ V}$	0.70V _{CC(A)}	-	0.70V _{CC(A)}	-	٧
		$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}$	$0.65V_{CC(A)}$	-	$0.65V_{CC(A)}$	-	٧
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	1.6	-	٧
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	2	-	2	-	V

^[2] V_{CCI} is the supply voltage associated with the data input port.

^[3] For I/O ports, the parameter IOZ includes the input leakage current.

Table 7. Static characteristics ... continued [1][2]

At recommended operating conditions: voltages are referenced to GND (ground = 0.V)

Symbol	Parameter	Conditions	–40 °C t	o +85 °C	–40 °C to	+125 °C	Uni
			Min	Max	Min	Max	
√ _{IL}	LOW-level	data input					
	input voltage	V _{CCI} = 0.8 V	-	0.30V _{CCI}	-	0.30V _{CCI}	٧
		V _{CCI} = 1.1 V to 1.95 V	-	0.35V _{CCI}	-	0.35V _{CCI}	٧
		V _{CCI} = 2.3 V to 2.7 V	-	0.7	-	0.7	٧
		V _{CCI} = 3.0 V to 3.6 V	-	0.8	-	0.8	٧
		nDIR, nOE input					
		$V_{CC(A)} = 0.8 \text{ V}$	-	0.30V _{CC(A)}	-	0.30V _{CC(A)}	٧
		$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}$	-	0.35V _{CC(A)}	-	0.35V _{CC(A)}	٧
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	-	0.7	-	0.7	٧
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	-	0.8	-	0.8	٧
′он	HIGH-level	$V_I = V_{IH}$ or V_{IL}					
	output voltage	$I_O = -100 \ \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \ V$ to 3.6 V	V _{CCO} - 0.1	-	V _{CCO} - 0.1	-	٧
		$I_O = -3 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	0.85	-	0.85	-	٧
		$I_O = -6 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$		-	1.05	-	V
		$I_O = -8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	1.2	-	1.2	-	٧
		$I_O = -9 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	1.75	-	1.75	-	٧
		$I_{O} = -12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	2.3	-	2.3	-	٧
OL.	LOW-level	$V_I = V_{IH} \text{ or } V_{IL}$					
	output voltage	$\begin{array}{l} I_O = 100 \; \mu A; \\ V_{CC(A)} = V_{CC(B)} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	0.1	-	0.1	٧
		$I_O = 3 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	-	0.25	-	0.25	٧
		$I_O = 6 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	-	0.35	-	0.35	٧
		$I_O = 8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	-	0.45	-	0.45	٧
		$I_O = 9 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	-	0.55	-	0.55	٧
		$I_O = 12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	-	0.7	-	0.7	٧
	input leakage current	nDIR, n \overline{OE} input; V _I = 0 V or 3.6 V; V _{CC(A)} = V _{CC(B)} = 0.8 V to 3.6 V	-	±1	-	±5	μA
DΖ	OFF-state output current	A or B port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 3.6$ V	[3] _	±5	-	±30	μA
		suspend mode A port; $V_O = 0 \text{ V or } V_{CCO}; V_{CC(A)} = 3.6 \text{ V};$ $V_{CC(B)} = 0 \text{ V}$	[3] -	±5	-	±30	μΔ
		suspend mode B port; $V_O = 0 \text{ V or } V_{CCO}; V_{CC(A)} = 0 \text{ V};$ $V_{CC(B)} = 3.6 \text{ V}$	[3] -	±5	-	±30	μΑ

Table 7. Static characteristics ...continued [1][2]

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C 1	to +85 °C	–40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
I _{OFF}	power-off leakage	A port; V_1 or $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	±5	-	±30	μА
	current	B port; V_1 or $V_O = 0$ V to 3.6 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0.8$ V to 3.6 V	-	±5	-	±30	μΑ
I _{CC}	supply current	A port; $V_I = 0 V \text{ or } V_{CCI}$; $I_O = 0 A$					
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	30	-	125	μА
		$V_{CC(A)} = 1.1 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	25	-	100	μА
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-	25	-	100	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-5	-	-20	-	μΑ
		B port; $V_I = 0 \text{ V or } V_{CCI}$; $I_O = 0 \text{ A}$					
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	30	-	125	μА
		$V_{CC(A)} = 1.1 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	25	-	100	μА
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	- 5	-	-20	-	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-	25	-	100	μΑ
		A plus B port ($I_{CC(A)} + I_{CC(B)}$); $I_O = 0$ A; $V_I = 0$ V or V_{CCI} ; $V_{CC(A)} = 0.8$ V to 3.6 V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	55	-	185	μА
		A plus B port ($I_{CC(A)} + I_{CC(B)}$); $I_O = 0$ A; $V_I = 0$ V or V_{CCI} ; $V_{CC(A)} = 1.1$ V to 3.6 V; $V_{CC(B)} = 1.1$ V to 3.6 V	-	45	-	150	μА

^[1] V_{CCO} is the supply voltage associated with the output port.

Table 8. Typical total supply current $(I_{CC(A)} + I_{CC(B)})$

V _{CC(A)}	V _{CC(B)}	V _{CC(B)}						
	0 V	0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
0 V	0	0.1	0.1	0.1	0.1	0.1	0.1	μΑ
0.8 V	0.1	0.1	0.1	0.1	0.1	0.3	1.6	μΑ
1.2 V	0.1	0.1	0.1	0.1	0.1	0.1	0.8	μΑ
1.5 V	0.1	0.1	0.1	0.1	0.1	0.1	0.4	μΑ
1.8 V	0.1	0.1	0.1	0.1	0.1	0.1	0.2	μΑ
2.5 V	0.1	0.3	0.1	0.1	0.1	0.1	0.1	μΑ
3.3 V	0.1	1.6	0.8	0.4	0.2	0.1	0.1	μΑ

^[2] V_{CCI} is the supply voltage associated with the data input port.

^[3] For I/O ports, the parameter I_{OZ} includes the input leakage current.

10. Dynamic characteristics

Table 9. Typical power dissipation capacitance at $V_{CC(A)} = V_{CC(B)}$ and $T_{amb} = 25$ °C [1][2] Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions			V _{CC(A)} =	V _{CC(B)}			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
C_{PD}	power dissipation capacitance	A port: (direction nAn to nBn); output enabled	0.2	0.2	0.2	0.2	0.3	0.4	pF
		A port: (direction nAn to nBn); output disabled	0.2	0.2	0.2	0.2	0.3	0.4	pF
		A port: (direction nBn to nAn); output enabled	9	9.7	9.8	10.3	11.7	13.7	pF
		A port: (direction nBn to nAn); output disabled	0.6	0.6	0.6	0.7	0.7	0.7	pF
		B port: (direction nAn to nBn); output enabled	9	9.7	9.8	10.3	11.7	13.7	pF
		B port: (direction nAn to nBn); output disabled	0.6	0.6	0.6	0.7	0.7	0.7	pF
		B port: (direction nBn to nAn); output enabled	0.2	0.2	0.2	0.2	0.3	0.4	pF
		B port: (direction nBn to nAn); output disabled	0.2	0.2	0.2	0.2	0.3	0.4	pF

^[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

C_L = load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of the outputs.

[2] f_i = 10 MHz; V_I = GND to V_{CC} ; t_r = t_f = 1 ns; C_L = 0 pF; R_L = ∞ Ω .

Table 10. Typical dynamic characteristics at $V_{CC(A)} = 0.8 \text{ V}$ and $T_{amb} = 25 ^{\circ}\text{C}$ [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8; for wave forms see Figure 6 and Figure 7

Symbol	Parameter	Conditions	V _{CC(B)}						Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t_{pd}	propagation delay	nAn to nBn	14.4	7.0	6.2	6.0	5.9	6.0	ns
	nBn to nAn	14.4	12.4	12.1	11.9	11.8	11.8	ns	
t _{dis}	disable time	nOE to nAn	16.2	16.2	16.2	16.2	16.2	16.2	ns
		nOE to nBn	17.6	10.0	9.0	9.1	8.7	9.3	ns
t _{en}	enable time	nOE to nAn	21.9	21.9	21.9	21.9	21.9	21.9	ns
		nOE to nBn	22.2	11.1	9.8	9.4	9.4	9.6	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

Table 11. Typical dynamic characteristics at $V_{CC(B)} = 0.8 \text{ V}$ and $T_{amb} = 25 \text{ °C}$ [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8; for wave forms see Figure 6 and Figure 7

Symbol	Parameter	Conditions	V _{CC(A)}						
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t_{pd}	propagation delay	nAn to nBn	14.4	12.4	12.1	11.9	11.8	11.8	ns
		nBn to nAn	14.4	7.0	6.2	6.0	5.9	6.0	ns
t _{dis}	t _{dis} disable time	nOE to nAn	16.2	5.9	4.4	4.2	3.1	3.5	ns
		nOE to nBn	17.6	14.2	13.7	13.6	13.3	13.1	ns
t _{en} enable time	nOE to nAn	21.9	6.4	4.4	3.5	2.6	2.3	ns	
	nOE to nBn	22.2	17.7	17.2	17.0	16.8	16.7	ns	

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

Table 12. Dynamic characteristics for temperature range -40 °C to +85 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8; for wave forms see Figure 6 and Figure 7.

Symbol	Parameter	Conditions	V _{CC(B)}								Unit		
			1.2 V ± 0.1 V		1.5 V	± 0.1 V	1.8 V ±	0.15 V	2.5 V	± 0.2 V	3.3 V	± 0.3 V	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} =	1.1 V to 1.3 V				•	'	'	'			•		
t _{pd}	propagation	nAn to nBn	0.5	9.2	0.5	6.9	0.5	6.0	0.5	5.1	0.5	4.9	ns
	delay	nBn to nAn	0.5	9.2	0.5	8.7	0.5	8.5	0.5	8.2	0.5	8.0	ns
t _{dis}	disable time	n OE to nAn	1.5	11.6	1.5	11.6	1.5	11.6	1.5	11.6	1.5	11.6	ns
		n OE to nBn	1.5	12.5	1.5	9.7	1.5	9.5	1.0	8.1	1.0	8.9	ns
t _{en}	enable time	n OE to nAn	1.0	14.5	1.0	14.5	1.0	14.5	1.0	14.5	1.0	14.5	ns
		nOE to nBn	1.1	14.9	1.1	11.0	1.1	9.6	1.0	8.1	1.0	7.7	ns
V _{CC(A)} =	1.4 V to 1.6 V												
t_{pd}	propagation	nAn to nBn	0.5	8.7	0.5	6.2	0.5	5.2	0.5	4.1	0.5	3.7	ns
	delay	nBn to nAn	0.5	6.9	0.5	6.2	0.5	5.9	0.5	5.6	0.5	5.5	ns
t _{dis}	disable time	nOE to nAn	1.5	9.1	1.5	9.1	1.5	9.1	1.5	9.1	1.5	9.1	ns
		nOE to nBn	1.5	11.4	1.5	8.7	1.5	7.5	1.0	6.5	1.0	6.3	ns
t _{en}	enable time	nOE to nAn	1.0	10.1	1.0	10.1	1.0	10.1	1.0	10.1	1.0	10.1	ns
		nOE to nBn	1.0	13.5	1.0	10.1	0.5	8.1	0.5	5.9	0.5	5.2	ns
V _{CC(A)} =	1.65 V to 1.95	V											
t _{pd} propagation delay	nAn to nBn	0.5	8.5	0.5	5.9	0.5	4.8	0.5	3.7	0.5	3.3	ns	
	delay	nBn to nAn	0.5	6.0	0.5	5.2	0.5	4.8	0.5	4.5	0.5	4.4	ns
t _{dis}	disable time	nOE to nAn	1.5	7.7	1.5	7.7	1.5	7.7	1.5	7.7	1.5	7.7	ns
		nOE to nBn	1.5	11.1	1.5	8.4	1.5	7.1	1.0	5.9	1.0	5.7	ns
t _{en}	enable time	nOE to nAn	1.0	7.8	1.0	7.8	1.0	7.8	1.0	7.8	1.0	7.8	ns
		nOE to nBn	1.0	13.0	1.0	9.2	0.5	7.4	0.5	5.3	0.5	4.5	ns
V _{CC(A)} =	2.3 V to 2.7 V												
t _{pd}	propagation	nAn to nBn	0.5	8.2	0.5	5.6	0.5	4.6	0.5	3.3	0.5	2.8	ns
	delay	nBn to nAn	0.5	5.1	0.5	4.1	0.5	3.7	0.5	3.4	0.5	3.2	ns
t_{dis}	disable time	nOE to nAn	1.0	6.1	1.0	6.1	1.0	6.1	1.0	6.1	1.0	6.1	ns
		nOE to nBn	1.0	10.6	1.0	7.9	1.0	6.6	1.0	6.1	1.0	5.2	ns
t _{en}	enable time	nOE to nAn	0.5	5.3	0.5	5.3	0.5	5.3	0.5	5.3	0.5	5.3	ns
		nOE to nBn	0.5	12.5	0.5	9.4	0.5	7.3	0.5	5.1	0.5	4.5	ns
$V_{CC(A)} =$	3.0 V to 3.6 V												
t _{pd}	propagation	nAn to nBn	0.5	8.0	0.5	5.5	0.5	4.4	0.5	3.2	0.5	2.7	ns
	delay	nBn to nAn	0.5	4.9	0.5	3.7	0.5	3.3	0.5	2.9	0.5	2.7	ns
t _{dis}	disable time	nOE to nAn	0.5	5.0	0.5	5.0	0.5	5.0	0.5	5.0	0.5	5.0	ns
		nOE to nBn	1.0	10.3	1.0	7.7	1.0	6.5	1.0	5.2	0.5	5.0	ns
t _{en}	enable time	nOE to nAn	0.5	4.3	0.5	4.3	0.5	4.2	0.5	4.1	0.5	4.0	ns
		nOE to nBn	0.5	12.4	0.5	9.3	0.5	7.2	0.5	4.9	0.5	4.0	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

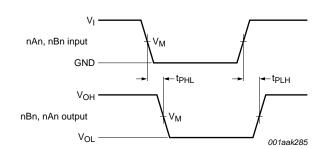
Table 13. Dynamic characteristics for temperature range -40 °C to +125 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8; for wave forms see Figure 6 and Figure 7

Symbol	Parameter	Conditions	V _{CC(B)}								Unit		
			1.2 V ± 0.1 V		1.5 V ± 0.1 V		1.8 V ± 0.15 V		2.5 V	± 0.2 V	3.3 V	± 0.3 V	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} =	1.1 V to 1.3 V	·									1		
t _{pd}	propagation	nAn to nBn	0.5	10.2	0.5	7.6	0.5	6.6	0.5	5.7	0.5	5.4	ns
	delay	nBn to nAn	0.5	10.2	0.5	9.6	0.5	9.4	0.5	9.1	0.5	8.8	ns
t _{dis}	disable time	nOE to nAn	1.5	12.8	1.5	12.8	1.5	12.8	1.5	12.8	1.5	12.8	ns
		nOE to nBn	1.5	13.8	1.5	10.7	1.5	10.5	1.0	9.0	1.5	9.8	ns
t _{en}	enable time	nOE to nAn	1.0	16.0	1.0	16.0	1.0	16.0	1.0	16.0	1.0	16.0	ns
		nOE to nBn	1.1	16.4	1.1	12.1	1.1	10.6	1.0	9.0	1.0	8.5	ns
V _{CC(A)} =	1.4 V to 1.6 V												
t _{pd}	propagation	nAn to nBn	0.5	9.6	0.5	6.9	0.5	5.8	0.5	4.6	0.5	4.1	ns
	delay	nBn to nAn	0.5	7.6	0.5	6.9	0.5	6.5	0.5	6.2	0.5	6.1	ns
t _{dis}	disable time	nOE to nAn	1.5	10.1	1.5	10.1	1.5	10.1	1.5	10.1	1.5	10.1	ns
		nOE to nBn	1.5	12.6	1.5	9.6	1.5	8.3	1.0	7.2	1.0	7.0	ns
t _{en}	enable time	nOE to nAn	1.0	11.2	1.0	11.2	1.0	11.2	1.0	11.2	1.0	11.2	ns
		nOE to nBn	1.0	14.9	1.0	11.2	0.5	9.0	0.5	6.5	0.5	5.8	ns
V _{CC(A)} =	1.65 V to 1.95	V											
t _{pd} propagation delay	nAn to nBn	0.5	9.4	0.5	6.5	0.5	5.3	0.5	4.1	0.5	3.7	ns	
	nBn to nAn	0.5	6.6	0.5	5.8	0.5	5.3	0.5	5.0	0.5	4.9	ns	
t _{dis}	t _{dis} disable time	nOE to nAn	1.5	8.5	1.5	8.5	1.5	8.5	1.5	8.5	1.5	8.5	ns
		nOE to nBn	1.5	12.3	1.5	9.3	1.5	7.9	1.0	6.5	1.0	6.3	ns
t _{en}	enable time	nOE to nAn	1.0	8.6	1.0	8.6	1.0	8.6	1.0	8.6	1.0	8.6	ns
		nOE to nBn	1.0	14.3	1.0	10.2	0.5	8.2	0.5	5.9	0.5	5.0	ns
V _{CC(A)} =	2.3 V to 2.7 V												
t _{pd}	propagation	nAn to nBn	0.5	9.1	0.5	6.2	0.5	5.1	0.5	3.7	0.5	3.1	ns
	delay	nBn to nAn	0.5	5.7	0.5	4.6	0.5	4.1	0.5	3.8	0.5	3.6	ns
t _{dis}	disable time	nOE to nAn	1.0	6.8	1.0	6.8	1.0	6.8	1.0	6.8	1.0	6.8	ns
		nOE to nBn	1.0	11.7	1.0	8.7	1.0	7.3	1.0	6.8	1.0	5.8	ns
t _{en}	enable time	nOE to nAn	0.5	5.9	0.5	5.9	0.5	5.9	0.5	5.9	0.5	5.9	ns
		nOE to nBn	0.5	13.8	0.5	10.4	0.5	8.1	0.5	5.7	0.5	5.0	ns
V _{CC(A)} =	3.0 V to 3.6 V												
t _{pd}	propagation	nAn to nBn	0.5	8.8	0.5	6.1	0.5	4.9	0.5	3.6	0.5	3.0	ns
	delay	nBn to nAn	0.5	5.4	0.5	4.1	0.5	3.7	0.5	3.2	0.5	3.0	ns
t _{dis}	disable time	nOE to nAn	0.5	5.5	0.5	5.5	0.5	5.5	0.5	5.5	0.5	5.5	ns
		nOE to nBn	1.0	11.4	1.0	8.5	1.0	7.2	1.0	5.8	0.5	5.5	ns
t _{en}	enable time	nOE to nAn	0.5	4.8	0.5	4.8	0.5	4.7	0.5	4.6	0.5	4.4	ns
		nOE to nBn	0.5	13.7	0.5	10.3	0.5	8.0	0.5	5.4	0.5	4.4	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

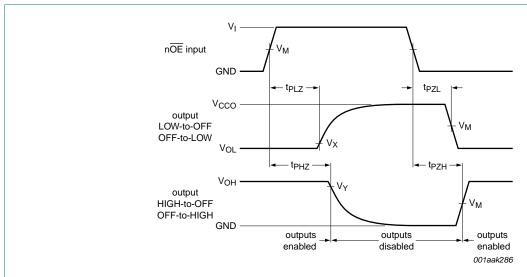
11. Waveforms



Measurement points are given in Table 14.

 $\ensuremath{V_{\text{OL}}}$ and $\ensuremath{V_{\text{OH}}}$ are typical output voltage levels that occur with the output load.

Fig 6. The data input (nAn, nBn) to output (nBn, nAn) propagation delay times



Measurement points are given in Table 14.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

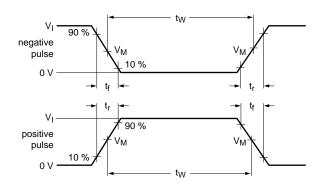
Fig 7. Enable and disable times

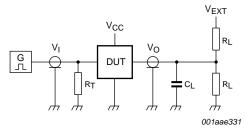
Table 14. Measurement points

Supply voltage	Input ^[1]	Output ^[2]					
V _{CC(A)} , V _{CC(B)}	V _M	V _M	V _X	V _Y			
0.8 V to 1.6 V	0.5V _{CCI}	0.5V _{CCO}	$V_{OL} + 0.1 V$	V _{OH} – 0.1 V			
1.65 V to 2.7 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} – 0.15 V			
3.0 V to 3.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	$V_{OH} - 0.3 V$			

^[1] V_{CCI} is the supply voltage associated with the data input port.

^[2] V_{CCO} is the supply voltage associated with the output port.





Test data is given in Table 15.

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance.

 V_{EXT} = External voltage for measuring switching times.

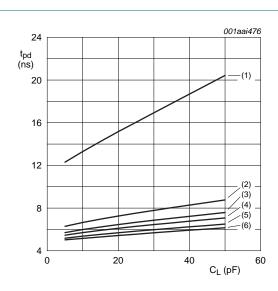
Fig 8. Test circuit for measuring switching times

Table 15. Test data

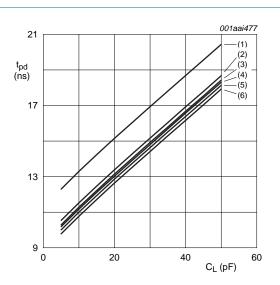
Supply voltage	Input		Load	Load		V _{EXT}		
V _{CC(A)} , V _{CC(B)}	V _I [1]	Δt/ΔV[2]	C _L	R _L	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} [3]	
0.8 V to 1.6 V	V_{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	
1.65 V to 2.7 V	V_{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	
3.0 V to 3.6 V	V_{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	

- [1] V_{CCI} is the supply voltage associated with the data input port.
- [2] $dV/dt \ge 1.0 V/ns$
- [3] V_{CCO} is the supply voltage associated with the output port.

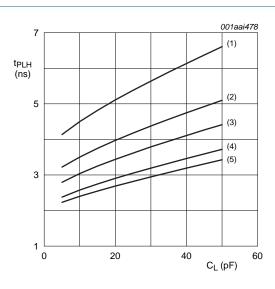
12. Typical propagation delay characteristics



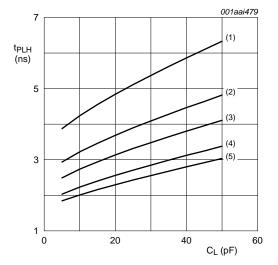
- a. Propagation delay (nAn to nBn); $V_{CC(A)} = 0.8 \text{ V}$
- (1) $V_{CC(B)} = 0.8 \text{ V}.$
- (2) $V_{CC(B)} = 1.2 \text{ V}.$
- (3) $V_{CC(B)} = 1.5 \text{ V}.$
- (4) $V_{CC(B)} = 1.8 \text{ V}.$
- (5) $V_{CC(B)} = 2.5 \text{ V}.$
- (6) $V_{CC(B)} = 3.3 \text{ V}.$



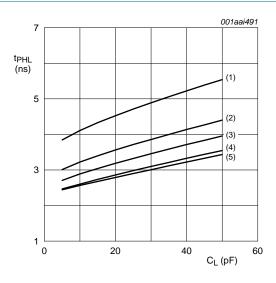
- b. Propagation delay (nAn to nBn); $V_{CC(B)} = 0.8 \text{ V}$
- (1) $V_{CC(A)} = 0.8 \text{ V}.$
- (2) $V_{CC(A)} = 1.2 \text{ V}.$
- (3) $V_{CC(A)} = 1.5 \text{ V}.$
- (4) $V_{CC(A)} = 1.8 \text{ V}.$
- (5) $V_{CC(A)} = 2.5 \text{ V}.$ (6) $V_{CC(A)} = 3.3 \text{ V}.$
- Fig 9. Typical propagation delay versus load capacitance; T_{amb} = 25 °C



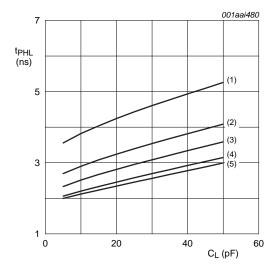
a. LOW to HIGH propagation delay (nAn to nBn); $V_{CC(A)} = 1.2 \text{ V}$



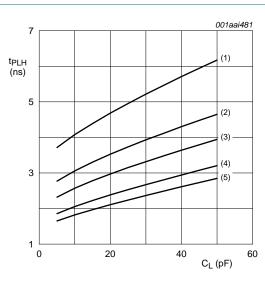
- c. LOW to HIGH propagation delay (nAn to nBn); $V_{CC(A)} = 1.5 \text{ V}$
- (1) $V_{CC(B)} = 1.2 \text{ V}.$
- (2) $V_{CC(B)} = 1.5 \text{ V}.$
- (3) $V_{CC(B)} = 1.8 \text{ V}.$
- (4) $V_{CC(B)} = 2.5 \text{ V}.$
- (5) $V_{CC(B)} = 3.3 \text{ V}.$



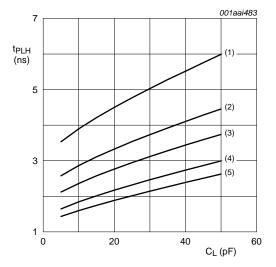
b. HIGH to LOW propagation delay (nAn to nBn); $V_{CC(A)} = 1.2 \text{ V}$



- d. HIGH to LOW propagation delay (nAn to nBn); $V_{CC(A)} = 1.5 \text{ V}$
- Fig 10. Typical propagation delay versus load capacitance; T_{amb} = 25 °C



a. LOW to HIGH propagation delay (nAn to nBn); $V_{CC(A)} = 1.8 \text{ V}$

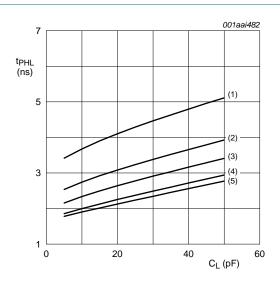


c. LOW to HIGH propagation delay (nAn to nBn); $V_{\text{CC(A)}} = 2.5 \text{ V}$

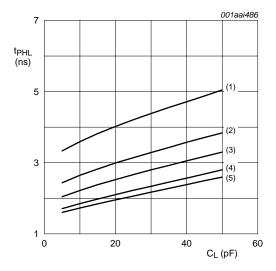


- (2) $V_{CC(B)} = 1.5 \text{ V}.$
- (3) $V_{CC(B)} = 1.8 \text{ V}.$
- (4) $V_{CC(B)} = 2.5 \text{ V}.$
- (5) $V_{CC(B)} = 3.3 \text{ V}.$





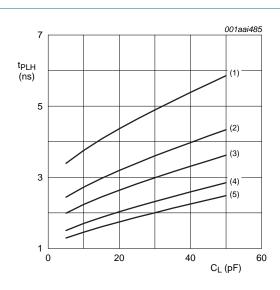
b. HIGH to LOW propagation delay (nAn to nBn); $V_{CC(A)} = 1.8 \text{ V}$

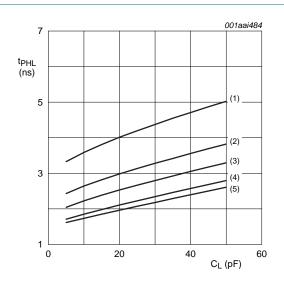


d. HIGH to LOW propagation delay (nAn to nBn); $V_{CC(A)} = 2.5 \text{ V}$

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16-bit dual supply translating transceiver; 3-state





- a. LOW to HIGH propagation delay (nAn to nBn);
 - $V_{CC(A)} = 3.3 \text{ V}$
- (1) $V_{CC(B)} = 1.2 \text{ V}.$
- (2) $V_{CC(B)} = 1.5 \text{ V}.$
- (3) $V_{CC(B)} = 1.8 \text{ V}.$
- (4) $V_{CC(B)} = 2.5 \text{ V}.$
- (5) $V_{CC(B)} = 3.3 \text{ V}.$

b. HIGH to LOW propagation delay (nAn to nBn); $V_{CC(A)} = 3.3 \text{ V}$

Fig 12. Typical propagation delay versus load capacitance; T_{amb} = 25 °C

13. Package outline

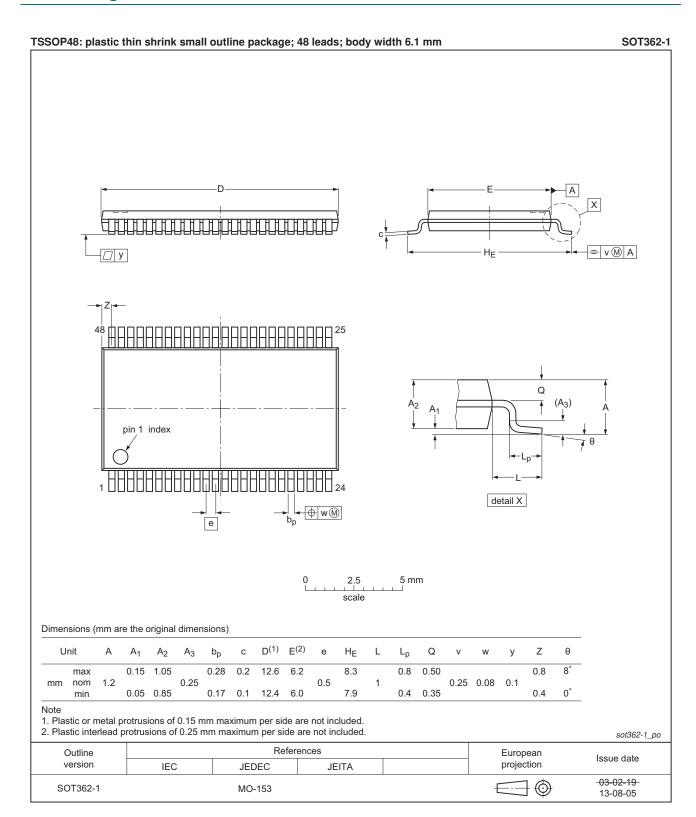
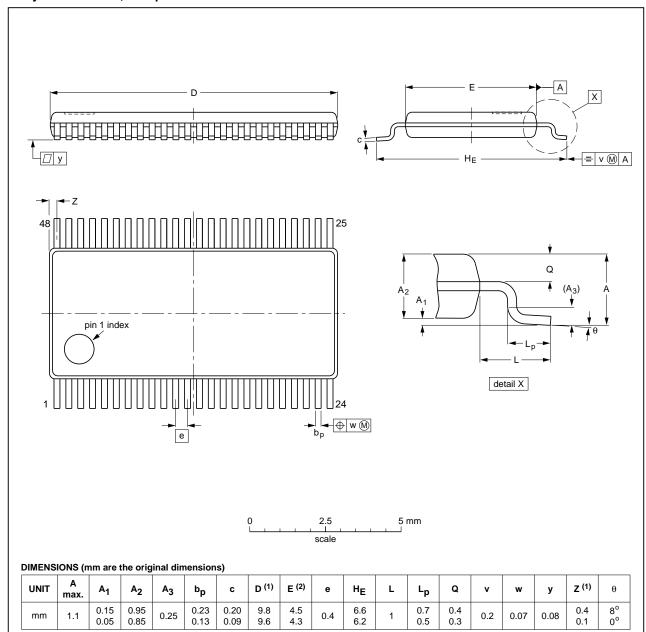


Fig 13. Package outline SOT362-1 (TSSOP48)

TSSOP48: plastic thin shrink small outline package; 48 leads; body width 4.4 mm; lead pitch 0.4 mm

SOT480-1



Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT480-1		MO-153				-99-12-27- 03-02-18	

Fig 14. Package outline SOT480-1 (TSSOP48)

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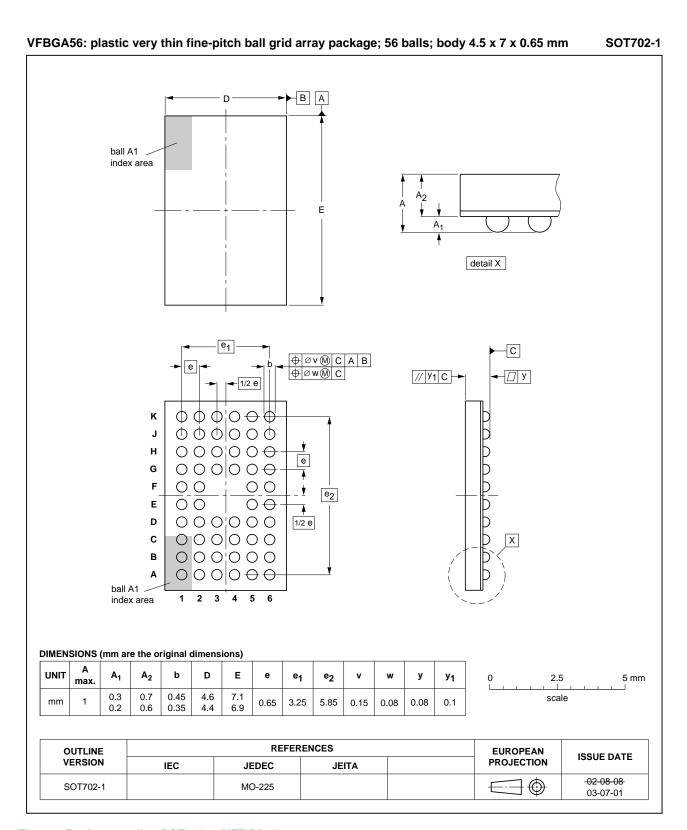


Fig 15. Package outline SOT702-1 (VFBGA56)

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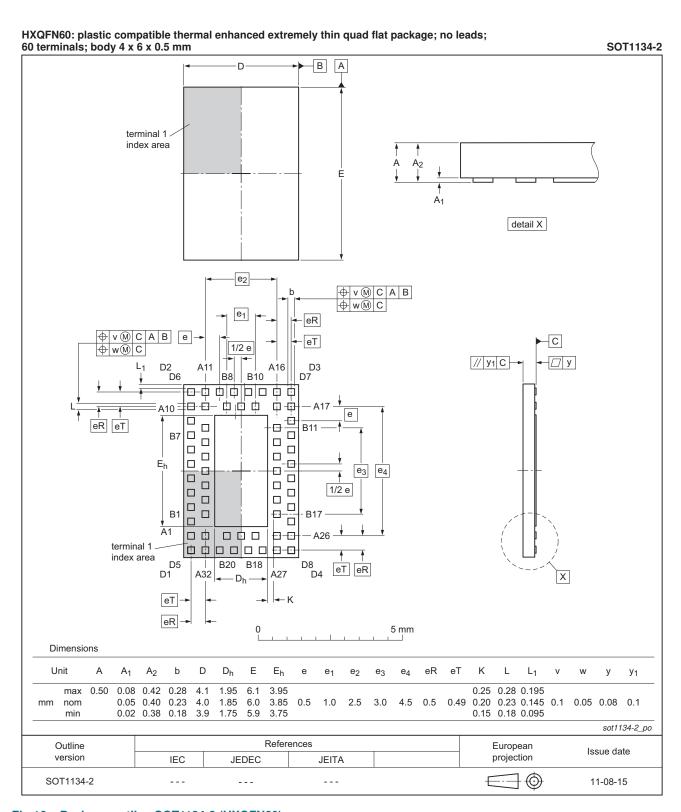


Fig 16. Package outline SOT1134-2 (HXQFN60)

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14. Abbreviations

Table 16. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

15. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AVC16T245 v.6	20130909	Product data sheet	-	74AVC16T245 v.5
Modifications:	• <u>Table 4</u> : con	ditions I_{CC} and I_{GND} change	d (errata).	
74AVC16T245 v.5	20120309	Product data sheet	-	74AVC16T245 v.4
Modifications:	 For type nur 	mber 74AVC16T245BX the s	ot code has changed to	SOT1134-2.
74AVC16T245 v.4	20111208	Product data sheet	-	74AVC16T245 v.3
Modifications:	 Legal pages 	updated.		
74AVC16T245 v.3	20110609	Product data sheet	-	74AVC16T245 v.2
74AVC16T245 v.2	20100330	Product data sheet	-	74AVC16T245 v.1
74AVC16T245 v.1	20091001	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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